

SOT-23



Pin Definition:

1. Base
2. Emitter
3. Collector

PRODUCT SUMMARY

BV_{CBO}	-60V
BV_{CEO}	-60V
I_C	-0.6A
V_{CE(SAT)}	-0.4V @ I _C / I _B = -150mA / -15mA

Features

- Low V_{CE(SAT)} -0.4 @ I_C / I_B = -150mA / -15mA
- Complementary part with TSC2411

Structure

- Epitaxial Planar Type
- PNP Silicon Transistor

Ordering Information

Part No.	Package	Packing
TSA1036CX RF	SOT-23	3Kpcs / 7" Reel

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V _{CBO}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-0.6	A
Collector Power Dissipation	P _D	225	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	556	°C/W
Operating Junction Temperature	T _J	+150	°C
Operating Junction and Storage Temperature Range	T _{STG}	- 55 to +150	°C

Note: Single pulse, Pw≤350us, Duty≤2%

Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	I _C = -10uA, I _E = 0	BV _{CBO}	-60	--	--	V
Collector-Emitter Breakdown Voltage	I _C = -10mA, I _B = 0	BV _{CEO}	-60	--	--	V
Emitter-Base Breakdown Voltage	I _E = -10uA, I _C = 0	BV _{EBO}	-5	--	--	V
Collector Cutoff Current	V _{CB} = -50V, I _E = 0	I _{CBO}	--	--	-10	nA
Emitter Cutoff Current	V _{EB} = -0.5V, I _C = 0	I _{EBO}	--	--	-50	nA
Collector-Emitter Saturation Voltage	I _C / I _B = -150mA / -15mA	*V _{CE(SAT)}	--	--	-0.4	V
Base-Emitter Saturation Voltage	I _C / I _B = -500mA / -50mA	*V _{BE(SAT)}	--	--	-1.3	V
DC Current Transfer Ratio	V _{CE} = -10V, I _C = -0.1A	*h _{FE} 1	75	--	--	
	V _{CE} = -10V, I _C = -150mA	*h _{FE} 2	100	--	300	
Transition Frequency	V _{CE} = -5V, I _C = -50mA, f = 100MHz	f _T	200	--	--	MHz
Output Capacitance	V _{CB} = -10V, f = 1MHz	Cob	--	--	8	pF

* Pulse Test: Pulse Width ≤380uS, Duty Cycle≤2%

Electrical Characteristics Curve ($T_a = 25^\circ\text{C}$, unless otherwise noted)

Figure 1. DC Current Gain

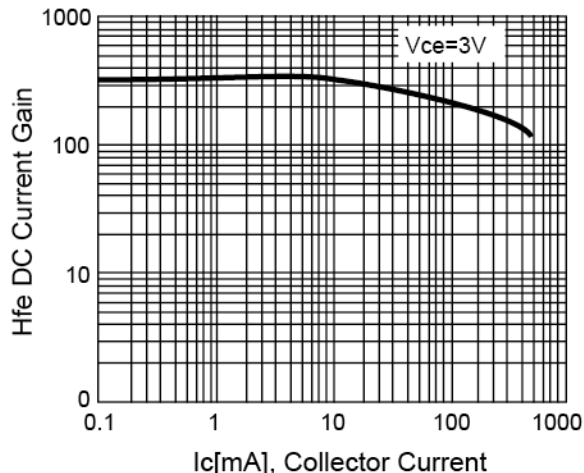


Figure 2. $V_{CE(SAT)}$ v.s. I_C

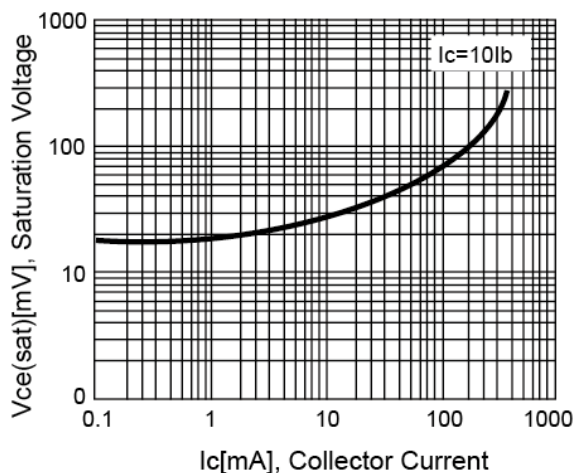


Figure 3. $V_{BE(SAT)}$ v.s. I_C

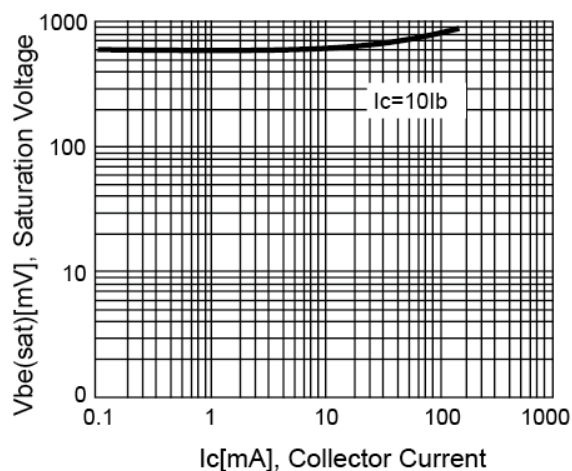


Figure 4. Cutoff Frequency vs. I_C

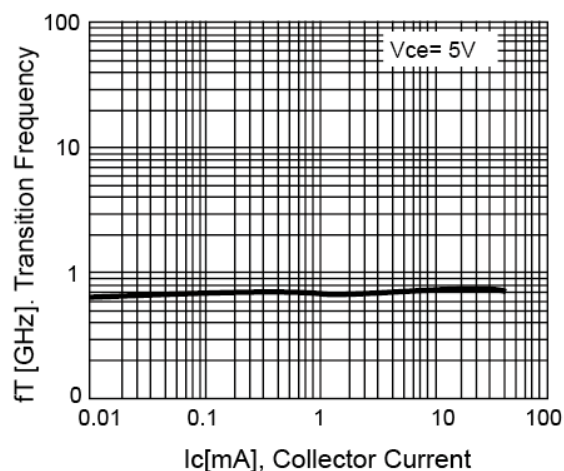
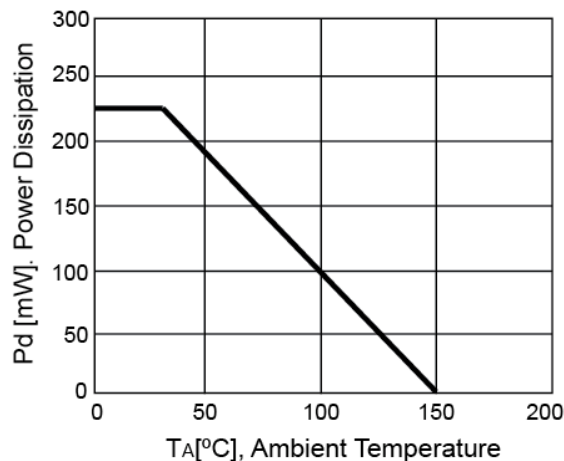
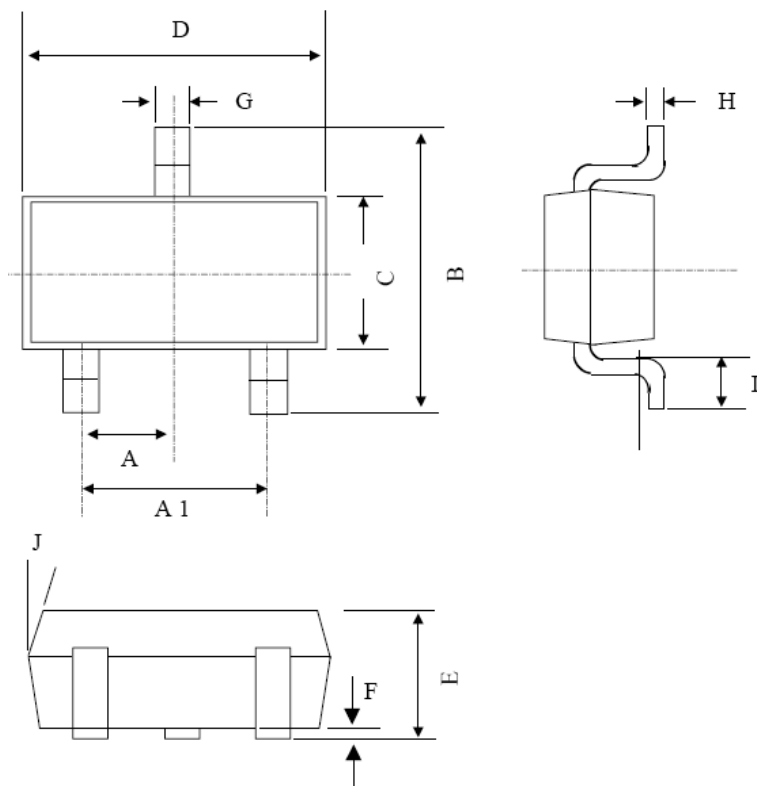


Figure 5. Power Derating Curve



SOT-23 Mechanical Drawing



DIM	SOT-23 DIMENSION			
	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX.
A	0.95 BSC		0.037 BSC	
A1	1.9 BSC		0.074 BSC	
B	2.60	3.00	0.102	0.118
C	1.40	1.70	0.055	0.067
D	2.80	3.10	0.110	0.122
E	1.00	1.30	0.039	0.051
F	0.00	0.10	0.000	0.004
G	0.35	0.50	0.014	0.020
H	0.10	0.20	0.004	0.008
I	0.30	0.60	0.012	0.024
J	5°	10°	5°	10°

TSA1036

General Purpose PNP Transistor

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